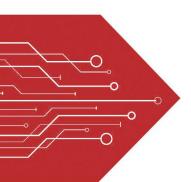
## MSKSEMI















**ESD** 

TVS

**TSS** 

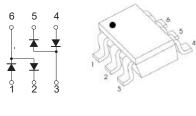
MOV

**GDT** 

**PLED** 

# Broduct data sheet





SOT-363

#### **MAKING: KJG**



### **BAV99DW**

**SWITCHING DIODE** 

#### **FEATURES**

- Fast Switching Speed
- Ultra-Small Surface Mount Package
- For General Purpose Switching Applications
- High Conductance

#### Maximum Ratings @Ta=25℃

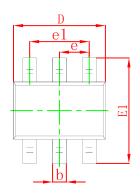
Parameter	Symbol	Limit	Unit
Peak Repetitive Peak Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	75	٧
Forward Continuous Current	I <sub>FM</sub>	300	mA
Average Rectified Output Current	Io	150	mA
Non-Repetitive Peak Forward Surge Current @ t=8.3 ms	I <sub>FSM</sub>	2.0	Α
Power Dissipation	P <sub>D</sub>	200	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	625	°C/W
Operating Junction Temperature	TJ	150	$^{\circ}$
Storage Temperature	T <sub>STG</sub>	-55~+150	${\mathfrak C}$

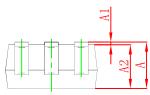
### **ELECTRICAL CHARACTERISTICS(T<sub>a</sub>=25℃ unless otherwise specified)**

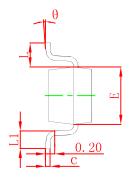
• • •						
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Reverse voltage	V <sub>(BR)</sub>	I <sub>R</sub> =2.5µA	75			V
Reverse current	1_	V <sub>R</sub> =75V			2.5	μA
	lR	V <sub>R</sub> =20V			25	nA
Forward voltage	VF	I=1mA			0.715	V
		I <sub>F</sub> =10mA			0.855	
		I=50mA			1	
		I=150mA			1.25	
Total capacitance	C <sub>tot</sub>	V <sub>R</sub> =0,f=1MHz			2	pF
Reverse recovery time	t <sub>rr</sub>	$I_F = I_R = 10 \text{mA}, I_{rr} = 0.1 \times I_R, R_L = 100 \Omega$			4	ns



## **SOT-363 Package Outline Dimensions**

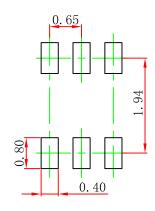






Symbol	Dimensions In Millimeters		Dimension	s In Inches
Syllibol	Min	Max	Min	Max
Α	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
С	0.100	0.150	0.004	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.400	0.085	0.094
е	0.650 TYP		0.026	S TYP
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

## **SOT-363 Suggested Pad Layout**



#### Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

#### **REEL SPECIFICATION**

P/N	PKG	QTY
BAV99DW	SOT-363	3000



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